

ABSTRACT

A method of etching silicon-containing film formed on an electrode layer of a floating potential is provided. The etching is performed in
5 a processing vessel while supplying gas, a first high frequency electric power of a first frequency, and a second high frequency electric power of a second frequency less than the first frequency. The method includes a step of supplying, during etching
10 of the silicon-containing film, the first high frequency electric power as a continuous wave and the second high frequency electric power as a pulse wave having a duty cycle of 20% or less, upon a distance from the electrode layer to a bottom of an
15 etching pattern formed on the silicon-containing film becoming not more than a predetermined distance.

Fig. 7